

U.S.S.N. 10/077,720

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Listing of the Claims

1. (cancelled)

2. (cancelled)

3. (cancelled)

4. (cancelled)

5. (cancelled)

6. (cancelled)

7. (cancelled)

8. (cancelled)

9. (Previously presented) The method of claim 1, wherein the first plasma etching process comprises supplying microwave power at a power level of from about 1000 to about 1500 Watts.

10. (currently amended) A method for plasma etching with improved etching selectivity for a low-K carbon containing dielectric material layer and underlying etch stop layer comprising the steps of:

providing a substrate comprising a low-K carbon containing dielectric material layer overlying a nitride containing etch stop underlayer;